

In the Claims:

Please amend claims 22, 26, 28, 30, 32, and 34 as follows:

22. (Three Times Amended) A microelectronic device, comprising:
a microelectronic substrate;

a gate structure including a gate oxide layer formed on the substrate, a first gate layer formed on the gate oxide layer, and an adhesion layer formed on the first gate layer, the gate structure having a trench at least partially disposed therein and extending into the substrate; and

a field oxide layer at least partially in the trench having substantially straight sides not contacting the gate oxide layer and extending upwardly from the trench and not extending laterally from the trench over an upper surface of the substrate, the field oxide layer having a field oxide level between the level of the upper surface of the substrate and the level of an upper surface of the first gate layer.

26. (Twice Amended) A microelectronic device, comprising:

a microelectronic substrate having a trench formed in a surface thereof;

a field oxide in the trench, the field oxide having substantially straight sides projecting outwardly from the trench beyond the surface of the substrate and not extending laterally from the trench over the surface of the substrate; and

a component formed on the field oxide, the component extending from the field oxide by a height at least equal to approximately two times a height that the field oxide extends from the trench beyond the surface of the substrate.

28. (Twice Amended) A microelectronic device, comprising:

a microelectronic substrate having a trench formed in a surface thereof;

a field oxide in the trench, the field oxide having substantially straight sides extending from the trench beyond the surface of the substrate and not extending laterally from the trench over the surface of the substrate; and

D3 cont

a gate structure formed on the substrate, the gate structure extending from the field oxide by a height at least equal to approximately two times a height that the field oxide extends from the trench beyond the surface of the substrate, the field oxide not contacting any portion of the gate structure.

D4

30. (Twice Amended) A microelectronic device, comprising:
 a microelectronic substrate having a recess formed in a surface thereof; and
 a field oxide deposited in the recess, the field oxide having substantially straight sides extending from the recess beyond the surface of the substrate by a height which is less than or equal to approximately one half of a height of a component formed on the field oxide, the field oxide not extending laterally from the recess over the surface of the substrate.

D5

32. (Three Times Amended) A microelectronic device, comprising:
 a microelectronic substrate having a trench formed in a surface thereof;
 a gate structure formed on the substrate, the gate structure including a gate oxide layer formed on the microelectronic substrate, a first gate layer formed on the gate oxide layer, an adhesion layer formed on the first gate layer, and a conductive layer formed on the adhesion layer; and
 a field oxide deposited in the trench, the field oxide extending from the trench beyond the surface of the substrate by a height which is less than or equal to approximately one half of a height of the gate structure formed on the substrate, the field oxide having substantially straight sides not contacting the gate oxide layer and not extending laterally from the recess over the surface of the substrate.

D6

34. (Twice Amended) A microelectronic device, comprising:
 a microelectronic substrate having a trench formed therein;
 a field oxide within the trench and having substantially straight sides projecting therefrom by a height which is small enough to prevent the formation of spacers adjacent the field oxide, the field oxide not extending laterally from the trench over the surface of the substrate; and
 a component formed on the field oxide.